

**CRYDOM**  
COMPANY

**POWER MODULES**

**SERIES L**

**13A-42.5A**

**SCR/DIODE CIRCUITS**

**Part Number Identification**

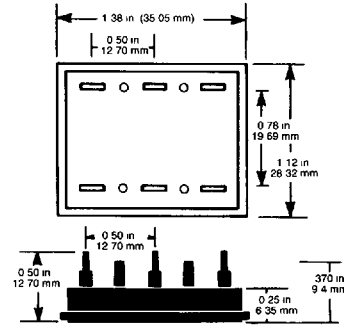
1st Digit Series Type	2nd Digit Current	3rd Digit Circuit Type	4th Digit AC Line Voltage	Options
L-Casestyle (Ceramic Base)	3-13 Amp 4-20 Amp. 5-25 Amp 6-42.5 Amp*	1-9 (see schematic diagrams)	1-120 volts 2-240 volts 3-280 volts	F-Free Wheeling Diode Option C-Gate to cathode capacitor option. Consult factory.

\* 42.5 AMP Rating only available in circuits 1, 2, 3, & 5.

Each part number consists of 4 to 7 digits. Use the table to determine the part that fits your needs.

**Electrical Specifications**

		SERIES			
		L3	L4	L5	L6*
$I_d$	maximum dc output current @ 85°C = Tc ceramic full bridge (A)	13.0	20	25	42.5
$I_{T_{RMS}}$	maximum output current @ 85°C = Tc CKT 5 (A)	15.0	22	27	46
$V_{TM}$	maximum SCR voltage (V) @ amperes peak	1.8V @ 13A	2.2V @ 20A	2.2V @ 25A	2.2V @ 40A
$I_H$	maximum holding current (mA)	100	100	100	200
$T_J$	operating junction temperature range	- 25°C to + 125°C			
di/dt	critical rate of rise of on-state current @ $T_J = 125°C$ (A/μS)	100	100	100	100
dv/dt	critical rate of rise of off-state current @ $T_J = 125°C$ (A/μS)	200	200	200	200
$V_{RMS}$	AC line input voltage	--- 120 (400PIV) --- --- 240 (600PIV) --- --- 280 (800PIV) --- --- 400 (1200PIV) ---			
$I_{TSM}$	maximum non-repetitive surge current (A)	150	250	300	600
$I^2t$	maximum $I^2t$ for fusing t = 8.3 (A² sec)	94	260	375	1500
$I_{GT}$	maximum required gate current to trigger, 25°C (mA)	100	100	100	100
$I_{GM}$	maximum peak gate current (A)	1.5	3.0	3.0	3.0
$V_{GT}$	maximum required gate voltage to trigger, 25°C (V)	2.5	2.5	2.5	3.0
$V_{GD}$	maximum non-triggering gate voltage at $T_J = 125°C$ (V)	0.2	0.2	0.2	0.2
$P_{GM}$	maximum peak gate power, $t_p = 10\mu\text{Sec.}$ (W)	5.0	5.0	5.0	5.0
$P_{G(AV)}$	average gate power (W)	0.5	0.5	0.5	0.5
$V_{GM}$	maximum peak gate voltage (reverse) (V)	5.0	5.0	5.0	5.0
$R_{OCs}$	maximum thermal resistance to sink (°C/W)	0.1	0.1	0.1	0.1
$R\theta_{JC}$	typical thermal resistance junction to ceramic base per device (°C/W)	0.6	0.5	0.5	0.5



**Circuit Configurations for Series L**

